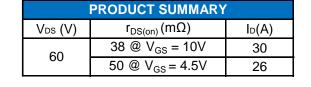
N-Channel 60-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

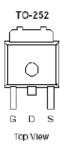
Typical Applications:

- PoE Power Sourcing Equipment
- PoE Powered Devices
- Telecom DC/DC converters
- White LED boost converters









ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage			±20	v	
Continuous Drain Current	T _C =25°C	I _D	30	А	
Pulsed Drain Current ^b			100	~	
Continuous Source Current (Diode Conduction)		ا _s	30	А	
Power Dissipation	T _C =25°C	PD	50	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{ extsf{ heta}JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	3	C/W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board, drain pad using 2 oz copper, value dependent on PC board thermal characteristics
- b. Pulse width limited by maximum junction temperature

Typical Electrica	Characteristics
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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = 20 V$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 48 V, V_{GS} = 0 V$			1	uA	
	I _{DSS}	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	UA	
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	34			А	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$			38	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_{D} = 17 \text{ A}$			50	11122	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		22		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.86		V	
Dynamic							
Total Gate Charge	Qg			16.5		nC	
Gate-Source Charge	Q_gs	V_{DS} = 30 V, V_{GS} = 4.5 V, I_{D} = 20 A		5.3			
Gate-Drain Charge	Q_{gd}			8.6			
Turn-On Delay Time	t _{d(on)}			10.0			
Rise Time	t _r	V_{DD} = 30 V, R_{L} = 1.5 Ω , I_{D} = 20 A,		12.8		ne	
Turn-Off Delay Time	t _{d(off)}	V_{GEN} = 10 V, R_{GEN} = 6 Ω		53.1		ns	
Fall Time	t _f			18.6			
Input Capacitance	C _{iss}			1711			
Output Capacitance	C _{oss}	V_{DS} = 15 V, V_{GS} = 0 V, f =1 MHz		147		pF	
Reverse Transfer Capacitance	C _{rss}			134			

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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3

0.9

1.2

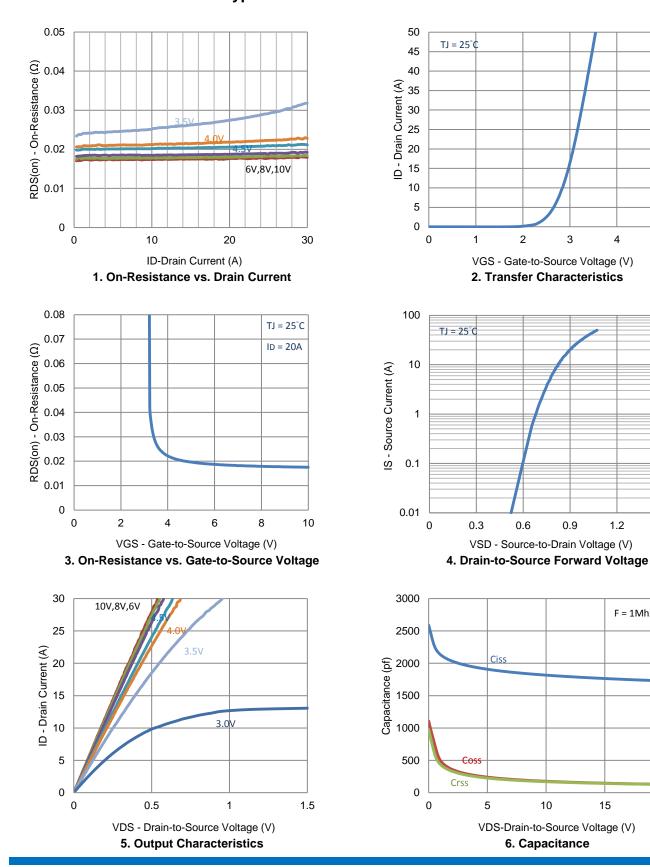
F = 1Mhz

1.5

20

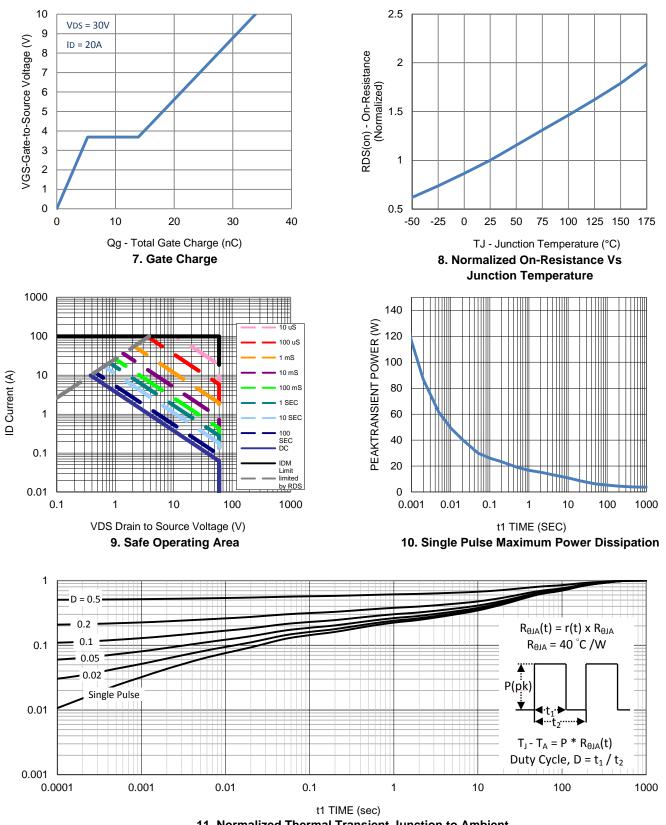
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5



Typical Electrical Characteristics

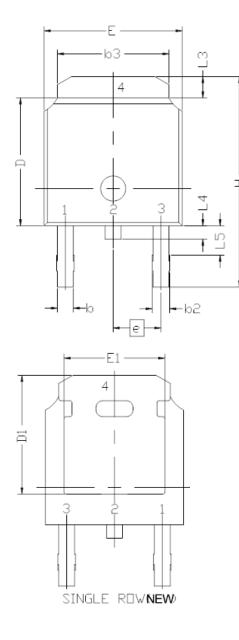
15

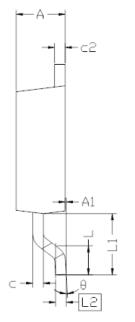


Typical Electrical Characteristics

11. Normalized Thermal Transient Junction to Ambient

Package Information





	DIMENS:	IONAL F	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1		2.743 RI	
L2		508 BS	-
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6.223
Н	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e		286 BS	
A	2.20	2.30	2.38
A1	0		0.127
C	0.45	0.50	0.60
c2	0,45	0.50	0.58
D1	5.30		
E1	4.40		
θ	0°		10*

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.